

	Type	Hits	Search Text	DBs
1	IS&R	2	("4159417").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
2	IS&R	0	("(Semiconductor or silicon or polysilicon or (silicon adj carbide) or (silicon adj carbide) or sic or gaas or gallium)near3substrate").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
3	BRS	449672	(Semiconductor or silicon or polysilicon or (silicon adj carbide) or sic or gaas or gallium) near3 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
4	BRS	7933	sensor and display and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
5	BRS	1232	(strain or gauge or gauges) and S4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
6	BRS	419	(pixel or pixels) and S5	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
7	BRS	129	S6 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
8	BRS	190	S6 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
9	BRS	260	S7 S8	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
10	BRS	281	Mems near15 (display or led or leds) and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
11	BRS	23	S10 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
12	BRS	22	S10 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
13	BRS	43	S11 S12	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
14	BRS	32	(logic or cmos or process\$4) and S13	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
15	BRS	478	((solar near (cell or sensor)) near15 display) and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
16	BRS	143	S15 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
17	BRS	42	S15 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
18	BRS	164	S17 S16	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
19	BRS	1073	Mems near5 (integrat\$3) and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
20	BRS	85	S19 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
21	BRS	84	S19 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
22	BRS	152	S20 S21	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
23	BRS	36	display and S22	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
24	IS&R	2	("5,536,988").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
25	BRS	483	(Mems near5 (logic or cmos)) and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
26	BRS	641	(Mems near15 (logic or cmos)) and S3	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
27	BRS	89	S25 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
28	BRS	96	S26 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
29	BRS	49	S26 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
30	BRS	140	S28 S29	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
31	BRS	77	(display or led or leds or pixel or pixels) and S30	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
32	BRS	126	mems.ti. and display	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
33	BRS	1	S32 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
34	BRS	6	S32 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
35	BRS	7	S33 S34	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
36	BRS	46	mems.ti. and LEd	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
37	BRS	0	S36 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
38	BRS	3	S36 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
39	BRS	0	mems.ti. and "integrat\$4.ti"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
40	BRS	1406	mems.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
41	BRS	276594	integrat\$4.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
42	BRS	277910	S40 S41	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
43	BRS	90	S40 and S41	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
44	BRS	4	S43 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
45	BRS	1	S43 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
46	BRS	4	S44 S45	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
47	BRS	0	memes.clm. and "display.clm"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
48	BRS	208974	display.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
49	BRS	2084	mems.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
50	BRS	170	S48 and S49	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
51	BRS	3	S50 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
52	BRS	56	S50 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
53	BRS	57	S51 S52	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
54	BRS	1057	S49 and substrate.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
55	BRS	275	S54 and semiconductor.clm.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
56	BRS	4	S55 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
57	BRS	48	S55 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
58	BRS	50	S56 S57	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
59	IS&R	2	("5324980").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
60	IS&R	0	("quartznear15siliconnear15oxidiz\$4").PN.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
61	BRS	388	quartz near15 silicon near15 oxidiz\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
62	BRS	2474	quartz near3 forming	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
63	BRS	113	quartz near3 forming near15 oxid\$4	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
64	BRS	1433	quartz near1 (forming or process)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
65	BRS	1433	quartz near (forming or process)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
66	BRS	29	S64 same (silicon with oxid\$4)	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
67	BRS	21060	quartz.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
68	BRS	375126	substrate.ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
69	BRS	4364356	(forming or method or fabricating).ti.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
70	BRS	275	S67 and S68 and S69	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
71	BRS	1888256	transparent near15 semiconductor near3 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
72	BRS	1885736	transparent near5 semiconductor near3 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
73	BRS	583	transparent near2 semiconductor near1 substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
74	BRS	303	S73 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
75	BRS	67	S73 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
76	BRS	325	S74 S75	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
77	BRS	0	mems and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
78	BRS	41	led and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
79	BRS	109	display and S76	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
80	BRS	91	(transparent near semiconductor) near substrate	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB

	Type	Hits	Search Text	DBs
81	BRS	51	S80 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
82	BRS	11	S80 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
83	BRS	60	S81 S82	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
84	BRS	25	(liquid adj crystal adj display or lcd) and S80	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
85	BRS	6	S84 and @ad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
86	BRS	8	S84 and @rlad<"19990701"	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB
87	BRS	13	S85 S86	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB